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- Member of the Texas Instruments Widebus™ Family
- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- UBT[™] (Universal Bus Transceiver)
 Combines D-Type Latches and D-Type
 Flip-Flops for Operation in Transparent,
 Latched, or Clocked Mode
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

description

This 18-bit universal bus transceiver is designed for 1.65-V to 3.6-V V_{CC} operation.

Data flow in each direction is controlled by output-enable (OEAB and OEBA), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the high-to-low transition of CLKAB. Output-enable OEAB is active high. When OEAB is high, the B-port outputs are active. When OEAB is low, the B-port outputs are in the high-impedance state.

DGG OR DL PACKAGE (TOP VIEW)

	- 1				
OEAB	Q	1	\cup	56] GND
LEAB		2		55	CLKAB
A1		3		54] B1
GND		4		53] GND
A2	Ц	5		52	B2
A3	Ц	6		51] B3
V_{CC}	Q	7		50] v _{cc}
A4		8		49] B4
A5	_	9		48] B5
A6		10		• • •] B6
GND		11			GND
A7		12		45] B7
A8		13		44] B8
A9		14		43] B9
A10	Ц	15		42	B10
A11		16		41	B11
A12		17		40	B12
GND		18		39] GND
A13		19		38	B13
A14	q	20		37	B14
A15		21		36	B15
V_{CC}	Ц	22		35] v _{cc}
A16		23		34	B16
A17	Ц	24		33	B17
GND		25		32] GND
A18		26		31	B18
OEBA	g	27		30	CLKBA
LEBA	4	28		29] GND

Data flow for B to A is similar to that of A to B, but uses $\overline{\text{OEBA}}$, LEBA, and $\overline{\text{CLKBA}}$. The output enables are complementary (OEAB is active high, and $\overline{\text{OEBA}}$ is active low).

To ensure the high-impedance state during power up or power down, $\overline{\text{OEBA}}$ should be tied to V_{CC} through a pullup resistor and OEAB should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16500 is characterized for operation from -40°C to 85°C.



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FUNCTION TABLE†

	INPUTS						
OEAB	LEAB	CLKAB	Α	В			
L	Χ	Х	Х	Z			
Н	Н	Χ	L	L			
Н	Н	Χ	Н	Н			
Н	L	0	L	L			
Н	L	\downarrow	Н	Н			
Н	L	Н	Χ	в ₀ ‡ в ₀ §			
Н	L	L	Χ	в ₀ §			

[†]A-to-B data flow is shown; B-to-A flow is similar but

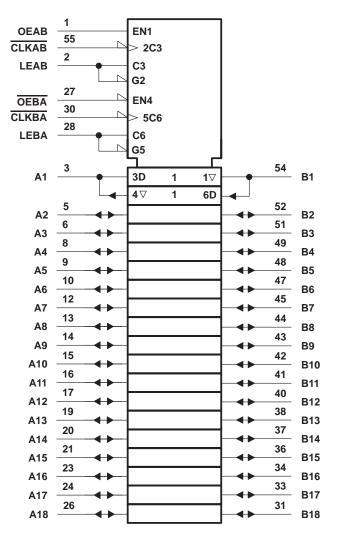
uses OEBA, LEBA, and CLKBA.

‡ Output level before the indicated steady-state input conditions were established, provided that CLKAB was high before LEAB went low

[§] Output level before the indicated steady-state input conditions were established

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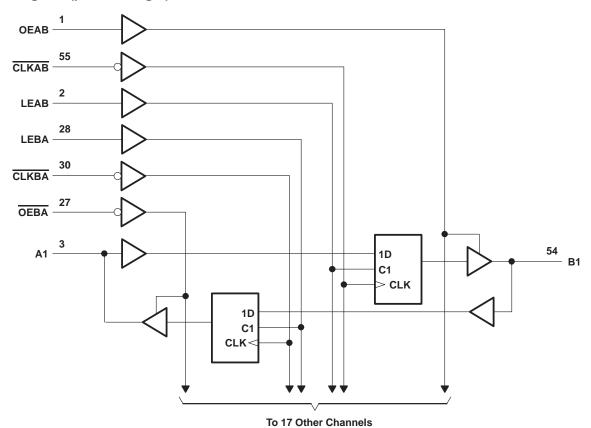
logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

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logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	0.5 V to 4.6 V
Input voltage range, V _I : Except I/O ports (see Note 1)	
I/O ports (see Notes 1 and 2)	
Output voltage range, VO (see Notes 1 and 2)	$-0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Input clamp current, $I_{ K }(V_1 < 0)$	
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, IO	±50 mA
Continuous current through each V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3): DGG package	64°C/W
DL package	56°C/W
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. This value is limited to 4.6 V maximum.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.



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recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
Vcc	Supply voltage		1.65	3.6	V	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V _{CC}			
ViH	$V_{CC} = 1.65 \ V \text{ to } 1.95$ $V_{CC} = 2.3 \ V \text{ to } 2.7 \ V$ $V_{CC} = 2.7 \ V \text{ to } 3.6 \ V$ $V_{CC} = 1.65 \ V \text{ to } 1.95$ $V_{CC} = 1.65 \ V \text{ to } 1.95$ $V_{CC} = 1.65 \ V \text{ to } 1.95$ $V_{CC} = 2.3 \ V \text{ to } 2.7 \ V$ $V_{CC} = 2.3 \ V \text{ to } 2.7 \ V$ $V_{CC} = 2.3 \ V \text{ to } 3.6 \ V$ $V_{CC} = 2.7 \ V \text{ to } 3.6 \ V$ $V_{CC} = 2.3 \ V$ $V_{CC} = 2.7 \ V$ $V_{CC} = 3 \ V$	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
		2				
	Low-level input voltage Input voltage Output voltage	V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}		
VIL	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
	Input voltage	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8		
٧ı	Input voltage		0	Vcc	V	
Vo	Output voltage		0	VCC	V	
		V _{CC} = 1.65 V		-4		
	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V _{CC} = 2.3 V		-12	m A	
IOH			-12	mA		
		$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	-24			
		V _{CC} = 1.65 V		4		
	V _{CC} = 2.3 V			12	mΛ	
IOL	Low-level output current	V _{CC} = 2.7 V		12	mA	
	V _{CC} = 3 V			24		
Δt/Δν	Input transition rise or fall rate			10	ns/V	
TA	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PAF	RAMETER	TEST CO	ONDITIONS	VCC	MIN	TYP [†]	MAX	UNIT		
		I _{OH} = -100 μA		1.65 V to 3.6 V	VCC-0	.2				
		I _{OH} = -4 mA		1.65 V	1.2					
		I _{OH} = -6 mA		2.3 V	2					
Vон				2.3 V	1.7			V		
		I _{OH} = -12 mA		2.7 V	2.2					
				3 V	2.4					
	I _{OH} = -24 mA		3 V	2						
		I _{OL} = 100 μA		1.65 V to 3.6 V			0.2			
		I _{OL} = 4 mA	1.65 V			0.45				
VOL	I _{OL} = 6 mA	2.3 V			0.4	V				
	lo. – 12 mA	2.3 V			0.7	v				
	I _{OL} = 12 mA	2.7 V			0.4					
		I _{OL} = 24 mA		3 V			0.55			
II		$V_I = V_{CC}$ or GND		3.6 V			±5	μΑ		
		V _I = 0.58 V	1.65 V	25						
		V _I = 1.07 V	1.65 V	-25						
		V _I = 0.7 V		2.3 V	45					
I _I (hold)		V _I = 1.7 V		2.3 V	-45			μΑ		
		V _I = 0.8 V		3 V	75					
		V _I = 2 V		3 V	-75					
		$V_{I} = 0 \text{ to } 3.6 \text{ V}^{\ddagger}$	3.6 V			±500				
IOZ§		$V_O = V_{CC}$ or GND		3.6 V			±10	μΑ		
ICC		$V_I = V_{CC}$ or GND,	IO = 0	3.6 V			40	μΑ		
Δlcc		One input at V _{CC} – 0.6 V,	Other inputs at V _{CC} or GND	3 V to 3.6 V			750	μΑ		
Ci	Control inputs	V _I = V _{CC} or GND		3.3 V		4		pF		
C _{io}	A or B ports	$V_O = V_{CC}$ or GND		3.3 V		8		pF		

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C. † This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

 $[\]mbox{\ensuremath{\,^\circ}}\mbox{For I/O}$ ports, the parameter $\mbox{\ensuremath{\,^\circ}}\mbox$

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timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

				V _{CC} =	1.8 V	V _{CC} =		V _{CC} =	2.7 V	V _{CC} =		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
fclock	Clock frequency				†		150		150		150	MHz
	Dulas duration	tion LE high CLK high or low		†		3.3		3.3		3.3		ns
t _w	Pulse duration			†		3.3		3.3		3.3		
	t _{su} Setup time	Data before CLK↓		†		1.7		1.4		1.3		
t _{su}		Data before LE↓	CLK high	†		1.1		1		1		ns
			CLK low	†		1.9		1.6		1.4		
		Data after CLK↓		†		1.7		1.6		1.3		
th	Hold time	Data after LE↓	CLK high	†		2		1.8		1.5		ns
			CLK low	†		1.6		1.5		1.2		

[†] This information was not available at the time of publication.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM	TO (OUTPUT)	V _{CC} =	1.8 V	V _{CC} =	2.5 V 2 V	VCC =	2.7 V	V _{CC} =	3.3 V 3 V	UNIT
	(INPUT)	(OUTPUT)	MIN	TYP	MIN	MAX	MIN	MAX	MIN	MAX	
f _{max}			†		150		150		150		MHz
	A or B	B or A		†	1	5.1		4.7	1	3.9	
^t pd	LEAB or LEBA	A or B		†	1	5.9		5.5	1	4.7	ns
•	CLKAB or CLKBA	AUID		†	1	6.6		6.6	1.1	5.5	
t _{en}	OEAB	В		†	1	5.7		5.4	1	4.6	ns
^t dis	OEAB	В		†	1	6.1		5.7	1.5	5	ns
t _{en}	OEBA	А		†	1	6.2		6.2	1	5.2	ns
^t dis	OEBA	А		†	1	5.4		4.6	1	4.3	ns

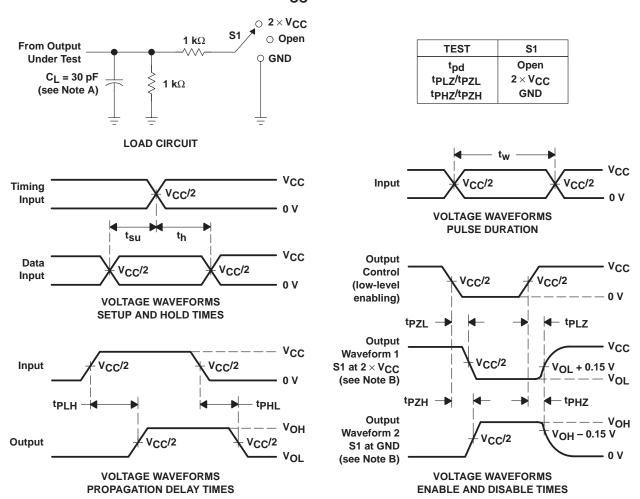
[†] This information was not available at the time of publication.

operating characteristics, $T_A = 25^{\circ}C$

PARAMETER			TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	UNIT
	FARAWETER		TEST CONDITIONS	TYP	TYP	TYP	ONIT
<u> </u>	Power dissipation	Outputs enabled	C ₁ = 50 pF. f = 10 MHz	†	40	51	pF
C _{pd}	capacitance	Outputs disabled	$C_L = 50 \text{ pF}, f = 10 \text{ MHz}$	†	6	6	ÞΓ

[†] This information was not available at the time of publication.

PARAMETER MEASUREMENT INFORMATION V_{CC} = 1.8 V



NOTES: A. C_L includes probe and jig capacitance.

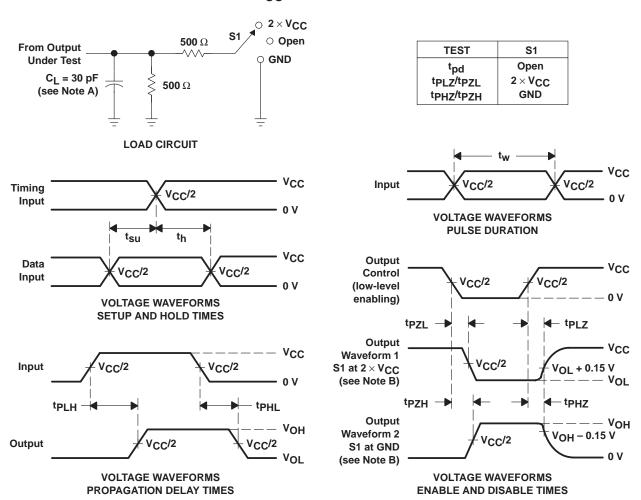
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as t_{dis}.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



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PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.5 V \pm 0.2 V

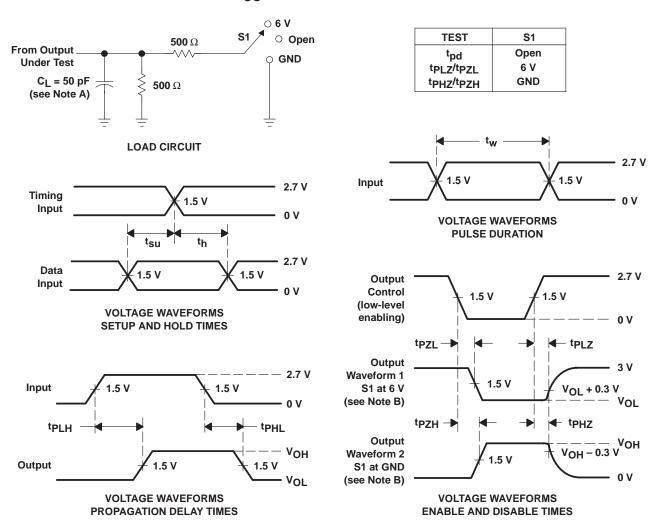


NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{O} = 50 $\Omega,\,t_{f}$ \leq 2 ns, t_{f} \leq 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{Ω} = 50 Ω , $t_{r} \leq$ 2.5 ns, $t_{f} \leq$ 2.5 ns,
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLZ and tpHZ are the same as tdis.
 - F. tpZL and tpZH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms



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